

CLM4426 / CLM4427 / CLM4428

FEATURES

- High Peak Output Current **>1.5A**
- Fast Switching **$t_D = 40\text{ns}$**
- Wide Operating Range **4.5V to 18V**
- Matched Rise and Fall Times
- ESD Protected **4kV**

APPLICATIONS

- Motor Controls
- Switch Mode Power Supplies
- Pulse Transformer Driver
- Class D Switching Amplifiers

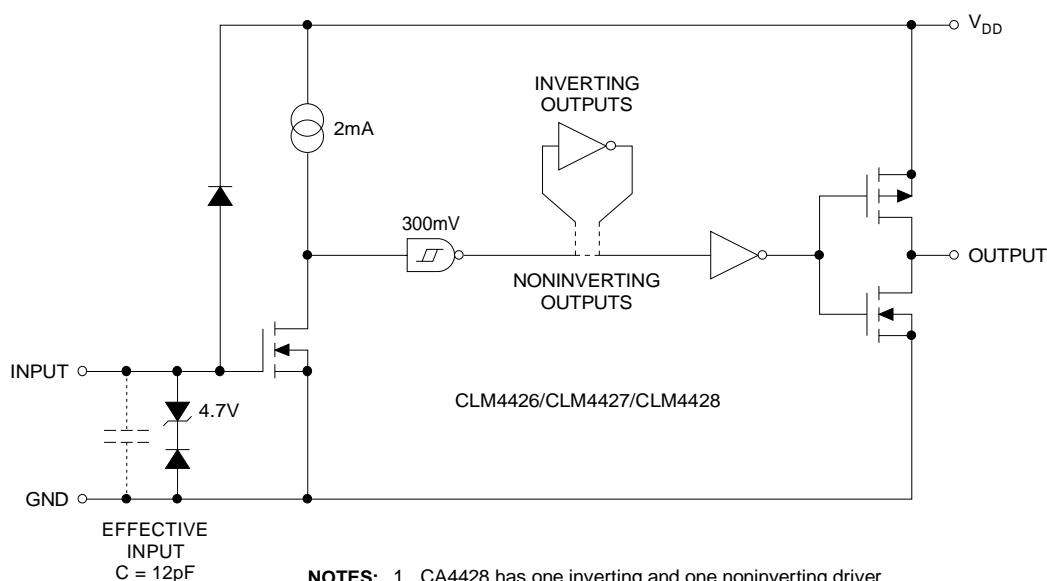
DESCRIPTION

The CLM4426 series are dual CMOS drivers are designed to drive capacitive, resistive and inductive loads switching 1000pF gate capacitances in under 30ns while providing low impedances in both the ON and OFF states to insure the MOSFET's intended state will not be affected. All terminals are fully protected up to 4kV of ESD.

ORDERING INFORMATION

Part	Logic	Package	Temperature
CLM4426CP	Inverting	8 Pin PDIP	0°C to 70°C
CLM4426EP	Inverting	8 Pin PDIP	-40°C to 85°C
CLM4426CY	Inverting	8 Pin SOIC	0°C to 70°C
CLM4426EY	Inverting	8 Pin SOIC	-40°C to 85°C
CLM4427CP	Noninverting	8 Pin PDIP	0°C to 70°C
CLM4427EP	Noninverting	8 Pin PDIP	-40°C to 85°C
CLM4427CY	Noninverting	8 Pin SOIC	0°C to 70°C
CLM4427EY	Noninverting	8 Pin SOIC	-40°C to 85°C
CLM4428CP	Differential	8 Pin PDIP	0°C to 70°C
CLM4428EP	Differential	8 Pin PDIP	-40°C to 85°C
CLM4428CY	Differential	8 Pin SOIC	0°C to 70°C
CLM4428EY	Differential	8 Pin SOIC	-40°C to 85°C

FUNCTIONAL DIAGRAM



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ABSOLUTE MAXIMUM RATINGS

Supply Voltage +22V
 Input Voltage, IN A or IN B $V_{DD}+0.3V$ to GND-5.0V
 Maximum Chip Temperature +150°C
 Storage Temperature Range -65°C to +150°C
 Lead Temperature (Soldering, 10 sec) +300°C
 Package Thermal Resistance

PDIP $R_{\theta JA}$ 125°C/W

PDIP $R_{\theta JC}$ 42°C/W

SOIC $R_{\theta JA}$ 250°C/W

SOIC $R_{\theta JC}$ 75°C/W

Operating Temperature Range

C Version 0°C to +70°C

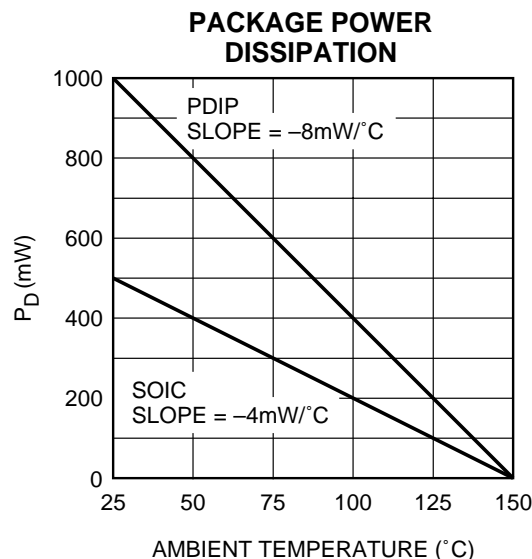
E Version -40°C to +85°C

Power Dissipation

Plastic 1000mW

SOIC 500mW

Static-sensitive device. Unused devices must be stored in conductive material. Protect devices from static discharge and static fields. Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions above those indicated in the operation sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



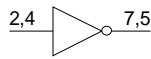
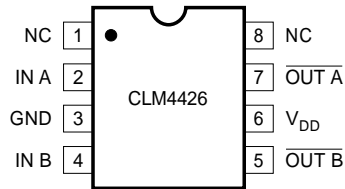
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ELECTRICAL CHARACTERISTICS $T_A = +25^\circ\text{C}$ with $4.5V \leq V_{DD} \leq 18V$, unless otherwise specified.

SYMBOL	PARAMETER	MIN	TYP	MAX	UNIT	TEST CONDITIONS
INPUT						
V_{IH}	Logic 1 High Input Voltage	2.4	-	-	V	
V_{IL}	Logic 0 Low Input Voltage	-	-	0.8	V	
I_{IN}	Input Current	-1	-	1	μA	$0V \leq V_{IN} \leq V_{DD}$
OUTPUT						
V_{OH}	High Output Voltage	$V_{DD}-0.025$	-	-	V	
V_{OL}	Low Output Voltage	-	-	0.025	V	
R_O	Output Resistance	-	7	10	Ω	$V_{DD} = 18V, I_O = 10\text{mA}$
I_{PK}	Peak Output Current	-	1.5	-	A	
I_{REV}	Latch-Up Protection Withstand Reverse Current	>0.5	-	-	A	Duty Cycle $\leq 2\%$ $t \leq 300\mu\text{s}$
SWITCHING TIME (Note 1)						
t_R	Rise Time	-	25	30	ns	Figure 1
t_F	Fall Time	-	25	30	ns	Figure 1
t_{D1}	Delay Time	-	-	30	ns	Figure 1
t_{D2}	Delay Time	-	-	50	ns	Figure 1
POWER SUPPLY						
I_S	Power Supply Current	-	-	4.5	mA	$V_{IN} = 3V$ (Both Inputs)
		-	-	0.4	mA	$V_{IN} = 0V$ (Both Inputs)

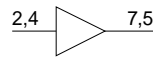
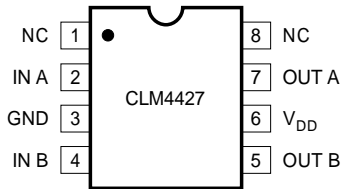
Note: 1. Switching times are guaranteed by design.

PIN CONFIGURATIONS

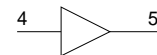
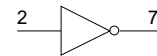
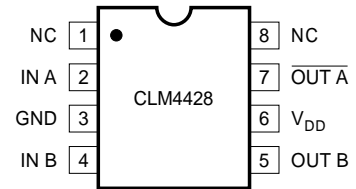


INVERTING

NC = NO INTERNAL CONNECTION



NONINVERTING



DIFFERENTIAL

NOTE: SOIC pinout is identical to DIP.

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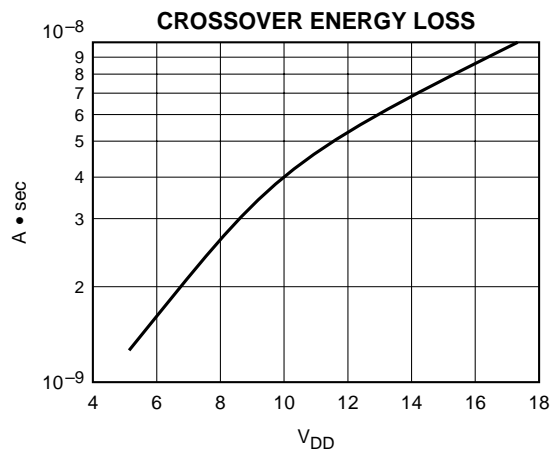
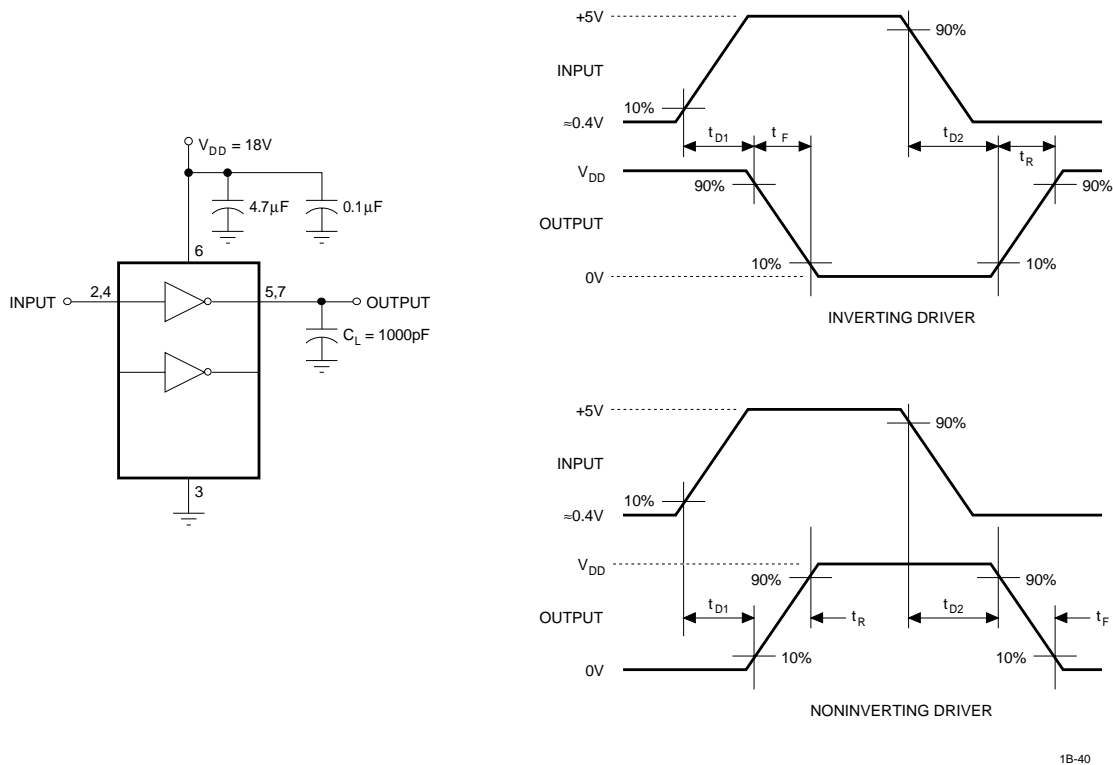
ELECTRICAL CHARACTERISTICS

Specifications measured over temperature range with $4.5V \leq V_{DD} \leq 18V$, unless otherwise specified.

SYMBOL	PARAMETER	MIN	TYP	MAX	UNIT	TEST CONDITIONS
INPUT						
V_{IH}	Logic 1 High Input Voltage	2.4	-	-	V	
V_{IL}	Logic 0 Low Input Voltage	-	-	0.8	V	
I_{IN}	Input Current	-1	-	1	μA	$0V \leq V_{IN} \leq V_{DD}$
OUTPUT						
V_{OH}	High Output Voltage	$V_{DD}-0.025$	-	-	V	
V_{OL}	Low Output Voltage	-	-	0.025	V	
R_O	Output Resistance	-	9	12	Ω	$V_{DD} = 18V, I_O = 10mA$
I_{PK}	Peak Output Current	-	1.5	-	A	
I_{REV}	Latch-Up Protection Withstand Reverse Current	>0.5	-	-	A	Duty Cycle $\leq 2\%$ $t \leq 300\mu s$
SWITCHING TIME (Note 1)						
t_R	Rise Time	-	-	40	ns	Figure 1
t_F	Fall Time	-	-	40	ns	Figure 1
t_{D1}	Delay Time	-	-	40	ns	Figure 1
t_{D2}	Delay Time	-	-	60	ns	Figure 1
POWER SUPPLY						
I_S	Power Supply Current	-	-	8	mA	$V_{IN} = 3V$ (Both Inputs)
		-	-	0.6	mA	$V_{IN} = 0V$ (Both Inputs)

Note: 1. Switching times are guaranteed by design.

FIGURE 1. SWITCHING TIME TEST CIRCUIT



NOTE: The values on this graph represent the loss seen by both drivers in a package during one complete cycle. For a single driver, divide the stated values by 2. For a single transition of a single driver, divide the stated value by 4.

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